BAV99WT1, SBAV99WT1G, BAV99RWT1, SBAV99RWT1G

Dual Series Switching Diodes

The BAV99WT1 is a smaller package, equivalent to the BAV99LT1.

Features

- These Devices are Pb−Free and are RoHS Compliant
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable

Suggested Applications

- ESD Protection
- Polarity Reversal Protection
- Data Line Protection
- Inductive Load Protection
- Steering Logic

MAXIMUM RATINGS (Each Diode)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	100	Vdc
Forward Current	I_F	215	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc
Repetitive Peak Reverse Voltage	V_{RRM}	70	V
Average Rectified Forward Current (Note 1) (averaged over any 20 ms period)	$I_{F(AV)}$	715	mA
Repetitive Peak Forward Current	I_{FRM}	450	mA
Non−Repetitive Peak Forward Current t = 1.0 μs t = 1.0 ms t = 1.0 s	I_{FSM}	 2.0 1.0 0.5	A

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR−5 = 1.0 × 0.75 × 0.062 in.

ON Semiconductor®

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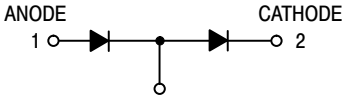
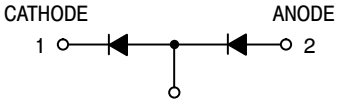
SC−70
CASE 419

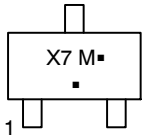


BAV99WT1
SC−70, CASE 419, STYLE 9



BAV99RWT1
SC−70, CASE 419, STYLE 10

MARKING DIAGRAM



A7 = BAV99WT1
F7 = BAV99RWT1
M = Date Code
▪ = Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping†
BAV99WT1G	SC−70 (Pb−Free)	3,000 / Tape & Reel
SBAV99WT1G	SC−70 (Pb−Free)	3,000 / Tape & Reel
BAV99RWT1G	SC−70 (Pb−Free)	3,000 / Tape & Reel
SBAV99RWT1G	SC−70 (Pb−Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

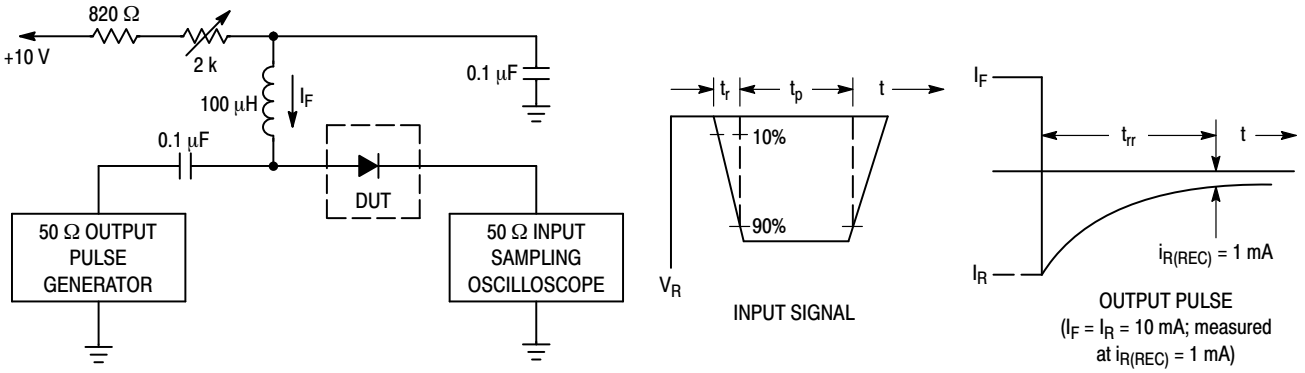
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board, (Note 1) T_A = 25°C Derate above 25°C	P_D	200 1.6	mW mW/°C
Thermal Resistance Junction−to−Ambient	$R_{\theta JA}$	625	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−65 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Each Diode)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage ($I_{(BR)}$ = 100 μA)	$V_{(BR)}$	100	–	Vdc
Reverse Voltage Leakage Current (V_R = 100 Vdc) (V_R = 25 Vdc, T_J = 150°C) (V_R = 70 Vdc, T_J = 150°C)	I_R	 – – –	 2.5 30 50	μAdc
Diode Capacitance (V_R = 0, f = 1.0 MHz)	C_D	–	1.5	pF
Forward Voltage (I_F = 1.0 mAdc) (I_F = 10 mAdc) (I_F = 50 mAdc) (I_F = 150 mAdc)	V_F	 – – – –	 715 855 1000 1250	mVdc
Reverse Recovery Time (I_F = I_R = 10 mAdc, $i_{R(REC)}$ = 1.0 mAdc) (Figure 1) R_L = 100 Ω	t_{rr}	–	6.0	ns
Forward Recovery Voltage (I_F = 10 mA, t_r = 20 ns)	V_{FR}	–	1.75	V

1. FR−5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.



Notes: (a) A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
(b) Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
(c) $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

CURVES APPLICABLE TO EACH DIODE

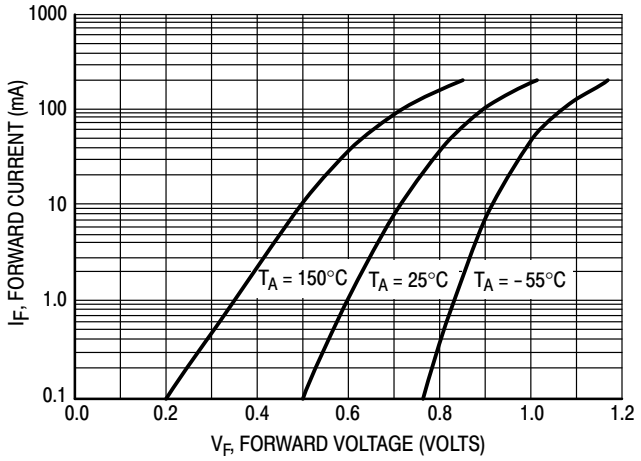


Figure 2. Forward Voltage

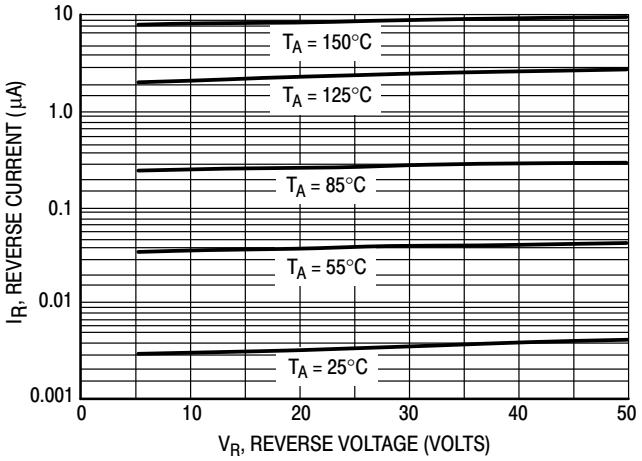


Figure 3. Leakage Current

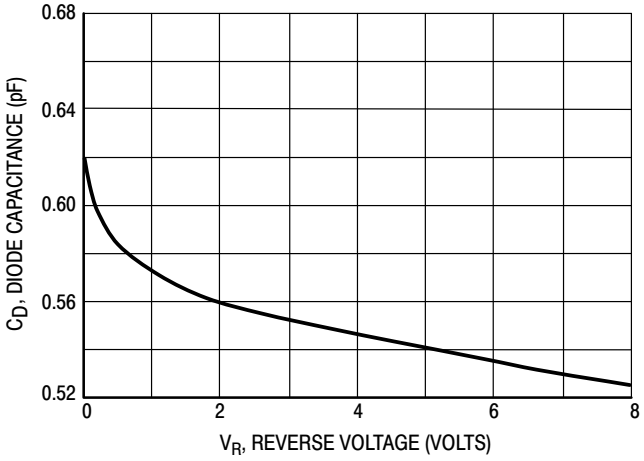
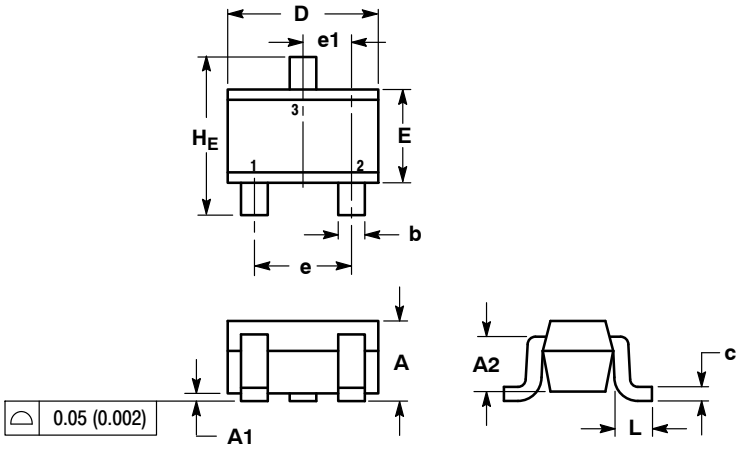


Figure 4. Capacitance

PACKAGE DIMENSIONS

SC−70 (SOT−323)
CASE 419−04
ISSUE N



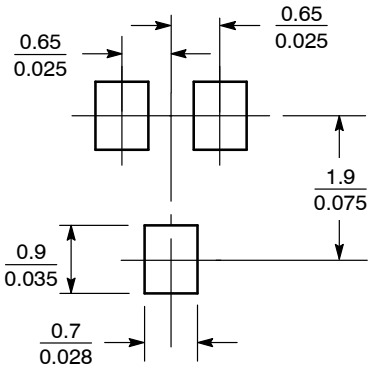
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF			0.028 REF	
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1		0.65 BSC			0.026 BSC	
L	0.20	0.38	0.56	0.008	0.015	0.022
H_E	2.00	2.10	2.40	0.079	0.083	0.095

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE

STYLE 10:
PIN 1. CATHODE
2. ANODE
3. ANODE-CATHODE

SOLDERING FOOTPRINT*



SCALE 10:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
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